

Silicon Power Transistors

2SD798

DESCRIPTION

- DARLINGTON
- High voltage
- With TO-220 package

APPLICATIONS

- With switching and igniter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	emitter

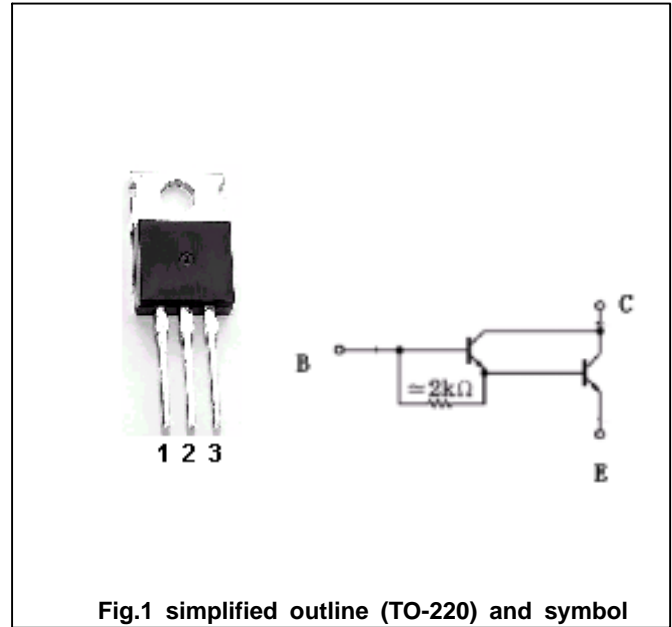


Fig.1 simplified outline (TO-220) and symbol

LIMITING VALUES

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	600	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_C	Collector dissipation	$T_C=25$	30	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =0.5A ;L=40mH	300			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A I _B =0.04A			2.0	V
V _{BEsat}	Emitter-base saturation voltage	I _C =4A I _B =0.04A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =600V I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.5	mA
h _{FE-1}	DC current gain	I _C =2A ; V _{CE} =2V	1500			
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =2V	200			
C _{OB}	Collector output capacitance	f=1MHz;V _{CB} =50V		35		pF

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PACKAGE OUTLINE

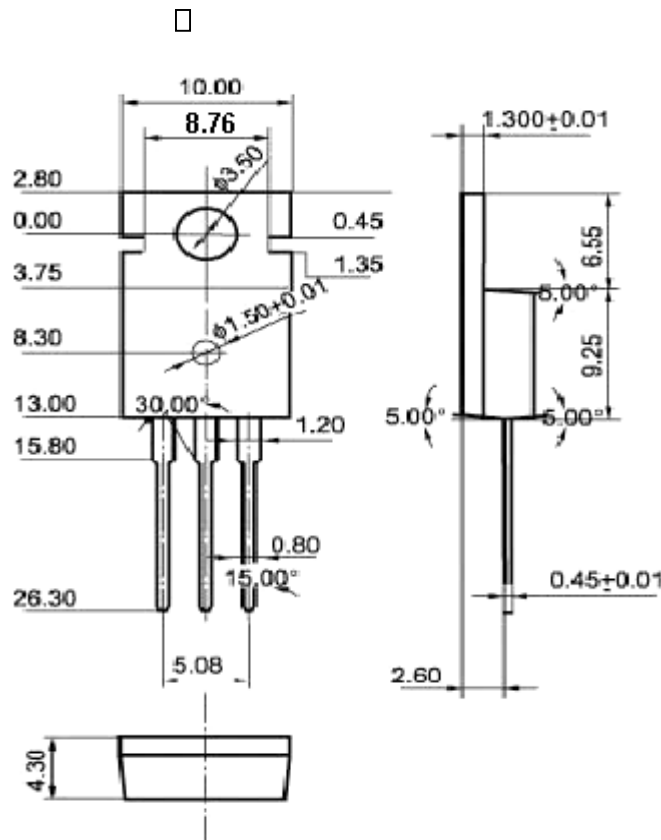


Fig.2 Outline dimensions